

Nam

Student ID:

Page:1/8

98  
/ 100

EE115A – Analog Electronic Circuits  
Fall 2017 – Prof. Shervin Moloudi  
Mid-term Exam – Monday November 6, 2017

READ THE INSTRUCTIONS BEFORE YOU START

- 1- You have 1 hour and 50 minutes.
- 2- Write your name on top of all pages and do not remove the staple.
- 3- If you need extra pages, ask the proctor.
- 4- A 5.5in x 8.5in 2-sided formula sheet is allowed.
- 5- No electronic devices including calculators, laptops, cell phones, etc. are allowed. You can use a regular wrist watch if you so choose.

Question	Points
1	/ 10
2	/ 40
3	/ 25
4	/ 25
Grade	/ 100



Name: [REDACTED]

Student ID: [REDACTED]

Page: 2/8

1- True or False?

T	In an NPN BJT the emitter is $N^+$ to ensure the BE current is dominated by free electrons.
F	In a PNP BJT the base layer is thin to ensure the rate of thermal ionization is sufficiently high.
F	N-type semiconductors are made by adding a dopant element from group V of the periodic table to a crystalline material of atoms from group III.
F	In a PN junction the width of the depletion region is larger on the P-side.
<del>F</del>	A semiconductor becomes more conductive as the temperature rises above the room temperature. $j_{ev} = \tau_{eov} b$

(2)

(10 points)



2- Find  $V_{out}$  versus  $V_{in}$ , as  $V_{in}$  varies from  $-\infty$  to  $+\infty$ , if the diodes have a turn on voltage of  $V_{Don}=0$  and are otherwise ideal (Use a piece-wise linear model).  $V_B$  is larger than 0.

(40 points)

1. Assume  $D_1, D_2, D_3$  off

$$I_1 = I_2 = I_3 = 0$$

By KCL: there's no current in the circuit.

$$V_{out} = R \cdot I_R = R \cdot 0 = 0V$$

Condition:  $V_{D1}, V_{D2}, V_{D3} < V_{D, on} = 0$

$$\textcircled{1} V_{D1} = V_{in} - V_B < 0$$

$$V_{in} < V_B$$

$$\textcircled{2} V_{D2} = V_{in} - V_B - V_B < 0$$

$$V_{in} < 2V_B$$

$\textcircled{3}$  By KVL

$$V_{D3} = V_B > 0$$

$\therefore V_{D3}$  is on, assumption fails.   
 *this case is impossible*

2. Assume  $D_1, D_2$  off,  $D_3$  on

$$I_{in} = I_2 = 0, I_3 > 0$$

$$I_{in} = I_1 + I_2 = 0$$

$$\therefore I_3 = \frac{V_B - V_{Don}}{2R} = \frac{V_B}{2R} > 0$$

$$V_{out} = -I_3 \cdot R = -\frac{V_B}{2}$$

Condition:

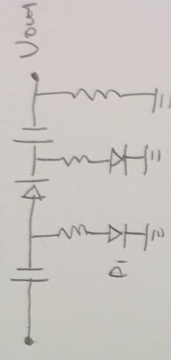
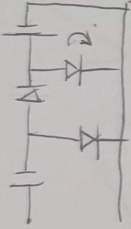
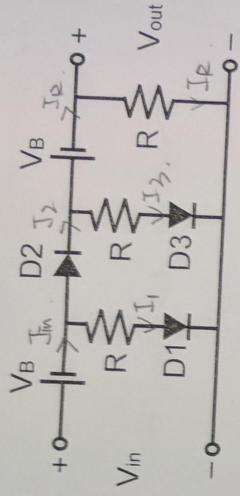
$$\textcircled{1} V_{D1} = V_{in} - V_B < 0$$

$$V_{in} < V_B$$

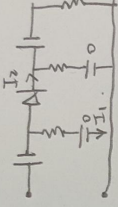
$$\textcircled{2} V_{D2} = V_{in} - V_B - R \cdot \frac{V_B}{2R} < 0$$

$$V_{in} < \frac{3}{2}V_B$$

$$\textcircled{1} \& \textcircled{2} : V_{in} < V_B$$



$\textcircled{3}$   $D_2$  off,  $D_1, D_3$  on.



$I_3$  is same as before

$$I_3 = \frac{V_B - 0}{2R} \Rightarrow V_{out} = -\frac{V_B}{2}$$

Conditions & verify:

$$\textcircled{1} I_3 = \frac{V_B}{2R} > 0 \Rightarrow D_3 \text{ is on, verified.}$$

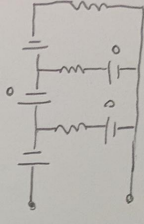
$$\textcircled{2} V_{D2} = V_{in} - V_B - 0 - \frac{V_B}{2} < 0$$

$$V_{in} < \frac{3}{2}V_B \checkmark$$

$$\textcircled{3} I_1 = \frac{V_{in} - V_B - 0}{R} > 0 \text{ for } V_{in} > V_B \text{ verified.}$$

$$\textcircled{1}, \textcircled{2} \& \textcircled{3} : V_B < V_{in} < \frac{3}{2}V_B$$

4. Last case:  $D_1, D_2, D_3$  on.



$$V_{out} = V_{in} - 2V_B$$

$$\textcircled{1} I_1 = \frac{V_{in} - V_B - V_B}{R} = I_3 > 0 \Rightarrow V_{in} > V_B$$

$$\textcircled{2} I_2 = \frac{V_{in} - V_B - V_B - 2V_B}{R} > 0 \Rightarrow V_{in} > \frac{5}{2}V_B$$

$$\textcircled{1} \& \textcircled{2} : V_{in} > \frac{5}{2}V_B$$

please see next page  $\rightarrow$

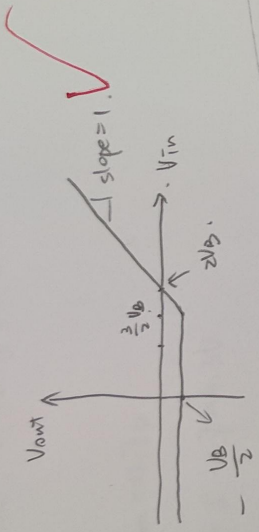
(19)

Name: [redacted] Student ID: [redacted] Page: 4/8

Sum up case 2, 3, 4:

$V_{out} = -\frac{V_B}{2}$  ,  $V_{in} < \frac{3}{2} V_B$  .  $\Rightarrow$  case 2, 3 together

$V_{out} = V_{in} - 2V_B$  ,  $V_{in} > \frac{3}{2} V_B$  .  $\Rightarrow$  case 4 .





Name: [REDACTED]

Student ID: [REDACTED]

Page: 5/8

3- Determine the terminal currents and the region of operation in this transistor circuit. Use a piecewise linear model for the diodes and assume  $V_{\text{Doff}} = 0.7\text{V}$ . In forward active mode  $\beta_F = 100$ ,  $V_{\text{BEon}} = 0.7\text{V}$ ,  $V_{\text{CEsat}} = 0.2\text{V}$ , and in reverse active mode  $\beta_R = 3$ ,  $V_{\text{BCon}} = 0.7\text{V}$ ,  $V_{\text{ECsat}} = 0.2\text{V}$ . (25 points)

Assume Q1 active, D1, D2, D3 are on;

$$V_E = 0\text{V}$$

$$V_B = 0 + V_{\text{BEon}} = 0.7\text{V}$$

$$V_1 = V_{\text{CC}} - V_{\text{D2}} = 5 - 0.7 = 4.3\text{V}$$

$$I_B = \frac{V_1 - V_B - V_{\text{D1}}}{R_B} = \frac{4.3 - 0.7 - 0.7}{290\text{k}}$$

$$= \frac{2.9}{290\text{k}} = 10\mu\text{A}$$

Verify

Since  $I_B > 0$ :  $\beta_{\text{BE}}$  Junction forward biased.

$D_1$  indeed on

$$I_C = \beta_F \cdot I_B = 100 \cdot 10\mu\text{A} = 1\text{mA}$$

$$I_E = I_B + I_C = 1.01\text{mA}$$

Verify

Since  $I_C = I_{\text{D3}} > 0$ ,  $D_3$  indeed on.

$I_E = I_{\text{D2}} > 0$ ,  $D_2$  indeed on.

$$V_C = V_{\text{CC}} - V_{\text{D2}} - V_{\text{D3}}$$

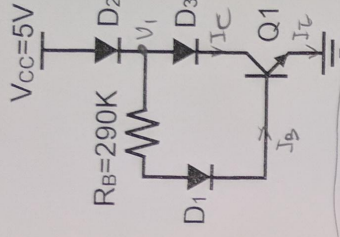
$$= 5 - 0.7 - 0.7 = 3.6\text{V}$$

$$\therefore V_{\text{CE}} = V_C - V_E = 3.6 - 0 = 3.6$$

$$\therefore V_{\text{CEsat}} = 0.2\text{V}$$

Verify

$V_{\text{CE}} > V_{\text{CEsat}}$   
also  $I_B > 0 \Rightarrow Q1$  is indeed in active mode.



$$\begin{cases} I_B = 10\mu\text{A} \\ I_C = 1\text{mA} \\ I_E = 1.01\text{mA} \end{cases} \quad \begin{cases} V_E = 0\text{V} \\ V_B = 0.7\text{V} \\ V_C = 3.6\text{V} \end{cases}$$

terminal currents  
& region of operation.